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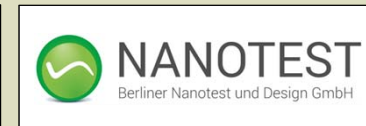
Design of a Four-Phase Mechanical Cycling Reliability Test Program and Evaluation Results for TIMs for Semiconductor Test Applications

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Purpose: TIM Contact Cycle Testing for Semiconductor Test

This presentation describes a reliability testing program for thermal interface materials (TIMs) for semiconductor test and burn-in applications:

- Survey, semiconductor test industry requirements for test parameters;
- Mechanical contact cycling and thermal resistance measurement of TIMs;
- Four program test phases, to test under increasingly rigorous cycling;
- Test results, Phases I - IV;
- Analysis.

The overall purpose of this test program is to evaluate durability of selected TIMs under mechanical contact cycling equivalent to semiconductor test.



Mechanical Cycling Reliability Test Program for Semiconductor Test

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Thermal Interface Materials

Thermal interface materials (TIM) are integral to adequate heat transfer from a semiconductor source to an external environment.

- Required for many different types of semiconductor packages and component interfaces.
- Typical requirement is for a single placement for an assembly, to contact the semiconductor device once only.

Specialized TIM materials are selected for challenging requirements for critical applications, including:

- Required thermal resistance value to meet a package heat transfer goal;
- Suitability for applicable surface flatness, roughness, available clamping force, operating environment.



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“Well-Performing” TIMs

What is meant by “well-performing”?

- No compound run-out due to temperature, for a polymer system;
- No dry-out of a carrier compound due to temperature;
- No compound pump-out due to mechanical stress, for a polymer system;
- No silicone bleed, outgassing, or redeposition on critical system elements for a silicone-containing polymer or thermal grease;
- No edge shredding, cracking, or other fragmentation for graphitic and metallic materials.



Mechanical Cycling Reliability Test Program for Semiconductor Test

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Thermal Interface Materials: Development Requirements

Table 2. TIM Typical Development Parameters

Thermal Impedance	Dielectric Strength**
Bond Line Thickness Post-Assembly	Cut-Through Resistance**
Thermal Conductivity	Thermal Cycling
Clamping Force Applied	Power Cycling
Wettability	Humidity and Bake
Thixotropy	HAST
Dispensing/Placement Process Automation	Shock and Vibration
Cure Schedule*	Flammability
Adhesion, Peel Test*	Working Life
Contaminants	Storage/Transit Temperature Range (As Supplied)
Modulus of Elasticity	Shipment/Storage Temp Range (Complete Assembly)
Material Stability	Removability and Rework Process
Silicone Stability	Environmental and Recycling Process
Flammability	Cost

Notes: * Applies only to adhesive TIMs. **Applies only to dielectric TIMs.

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Thermal Interface Materials for Semiconductor Test

Additional TIM application requirements specific to semiconductor test:

- Required product life and reliability;
- Durability for *multiple contact cycles with a single TIM: 50 – 5,000 cycles*;
- Ease of initial placement, rework, and cleaning;
- Zero residue or marking of DUT for semiconductor test applications;
- Ability to adapt to non-flat contact surface (“strike angle”);
- Resistance to high temperatures for testing and burn-in.

Proper TIM testing is critical to proper selection for each application.

Specific testing methods are needed to understand performance in unusual conditions for semiconductor test and burn-in applications.

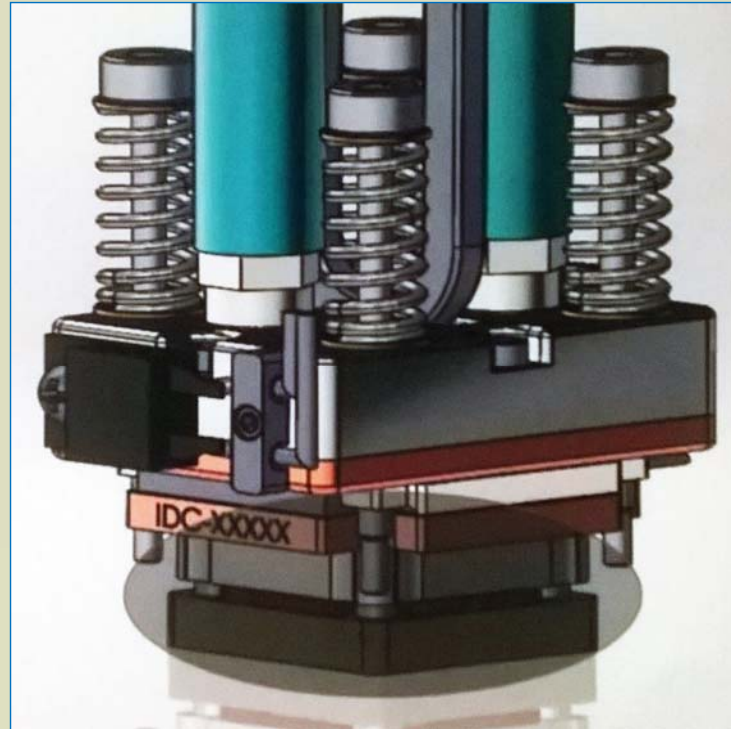
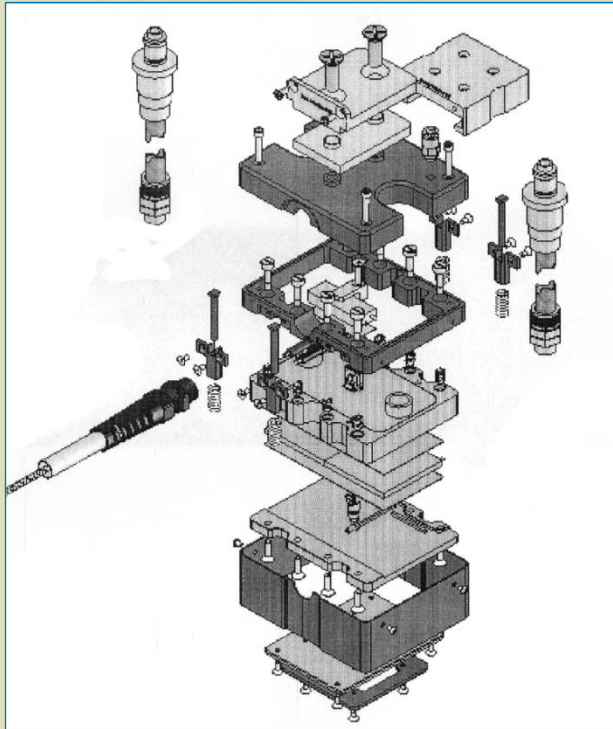


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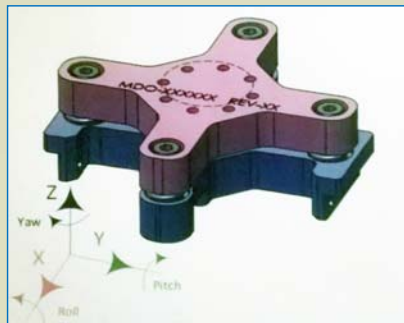
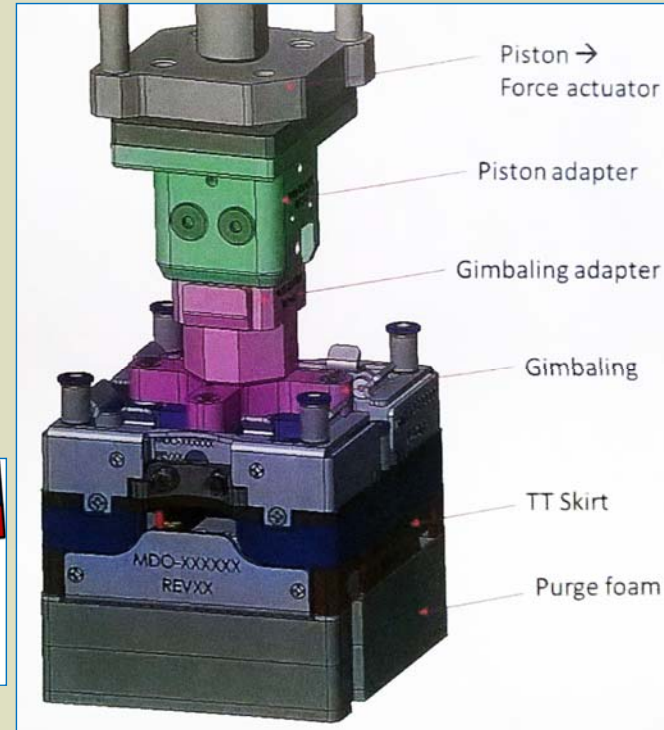
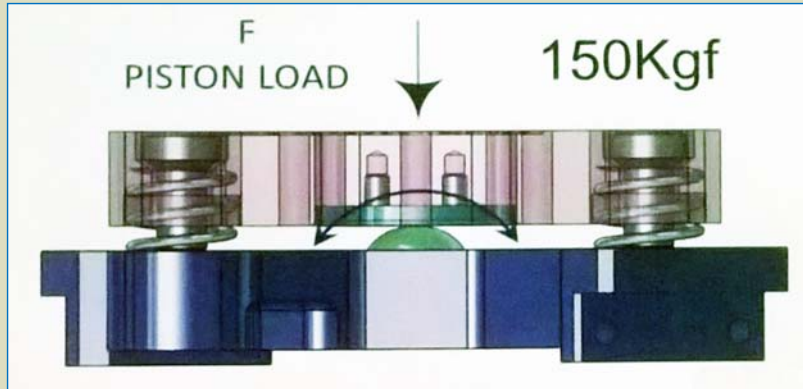


Semiconductor Test System Head Assemblies -- Examples

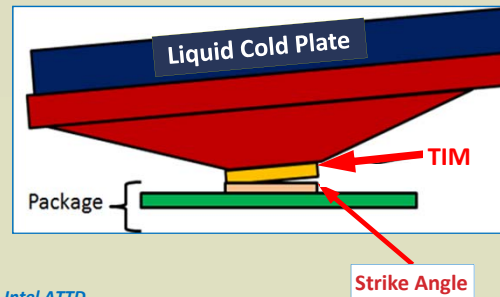


Sources for illustrations:
Left, Antares Advanced Test
Technologies, Inc..
Right, Intel ATTD.

Semiconductor Test System Head Assemblies -- Examples



Gimbaled Test Head Illustration



Source: DS&A LLC. Above: Intel IDC (Israel). Right: Intel ATTD.

Semiconductor Test Cycling Parameters

Semiconductor test engineers were surveyed to determine test parameters:

Table 3. Thermal /Mechanical Cycling Test Parameters

Organization	Test Pressure Reported	Test Temperature Range Reported (°C)	Dwell (Seconds)
Company A	11.7 bar (170 PSI)	25**/100	60
	11.7 bar (170PSI)	100	60
Company B	6.7 bar (100 PSI)	-	60
Company C	-	120	-
Company D	-	100	-
Company E	-	80	60
Company F	4.1/6.7 bar (60/100 PSI)*	105**/125	-
	6.7 bar (100 PSI)*	105**/125	-

*Note: * Pressure applied dependent upon die or package contact area. ** Initial value.
Source: DS&A LLC.*



Mechanical Cycling Reliability Test Program for Semiconductor Test

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Test Program Design: TIM Contact Cycling for Semiconductor Test

A test program with four phases for TIM thermal and reliability testing was designed to match requirements specific to semiconductor test and burn-in:

Table 1. Thermal /Mechanical Cycling Test Program Design

Program Phase	Purpose	Test Head Configuration*	Operating Temperature (°C)	Data Output
I	Baseline Values	Parallel	70 – 95	R_{th}^{**} , Thickness Change, ^{***} 1,000 Contact Cycles
II	Strike Angle	Upper Body: Strike Angle	70 – 95	R_{th}^{**} , Cycle Count
III	Strike Angle/Elevated Temperature	Upper Body: Strike Angle at Elevated Temperature	125	R_{th}^{**} , Cycle Count
IV	Baseline Values	Parallel	95	R_{th}^{**} , Thickness Change, ^{***} 5,000 Contact Cycles

Notes: * Test head configuration and test system design per ASTM D 5470-12 thermal interface material testing methodology. Use of this test system and methodology is intended to provide industry-standard baseline thermal performance values.

** Thermal resistance value is the principal thermal performance value for a TIM and uniform, stabilized values indicate an appropriately stable testing system.

*** Thickness change data is intended to provide indication of a stable test cycling process for baseline data.



Mechanical Cycling Reliability Test Program for Semiconductor Test

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Thermal/Mechanical Test System Design

Testing utilized a commercial ASTM D 5470-17 (modified) test stand:

Table 4. Thermal /Mechanical Cycling System Design	
Property	Value
System	Berliner Nanotest TIMA5
Upper Reference Body (Heater Bar)	125°C
Lower Reference Body (Liquid Cold Plate)	75°C
Sample Temperature	95°C
Clamping Force Method	Servo Automated
Clamping Force Applied	500kPa (5.0bar/72PSI)
Temperature Measurement	In situ
Thickness Measurement Under Force Applied	In situ

Note: Uniform single clamping force applied for all materials. Source: Berliner Nanotest und Design GmbH.

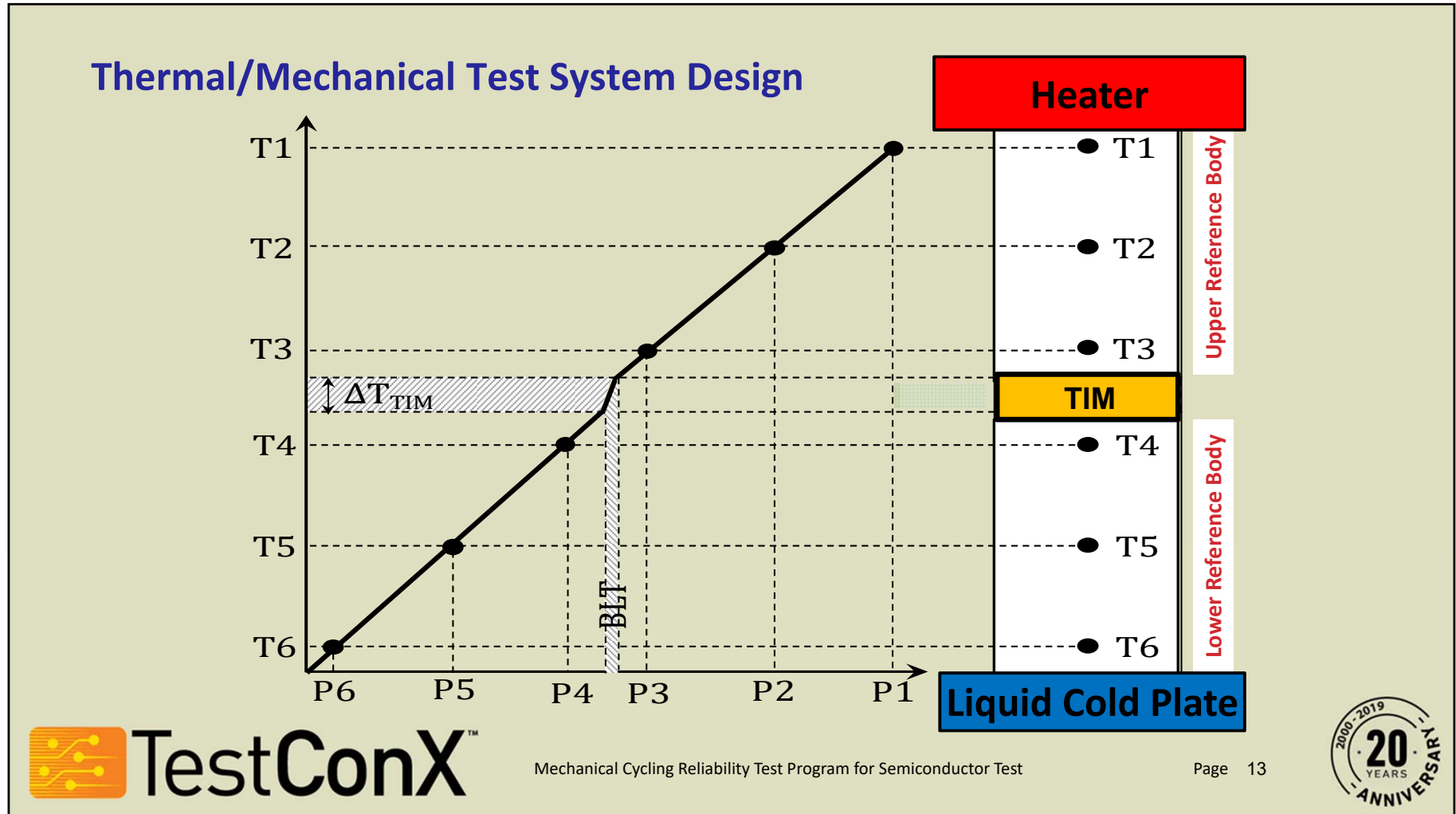
Thermal/Mechanical Test System Design

Berliner Nanotest commercial ASTM D 5470-17 TIM test stand utilized for this program:

- ASTM D 5470-17 is the industry standard test methodology for comparative TIM testing;
- System measures force applied, known power (heat) applied, temperature, thickness – with precise and uniform heat flow.
- Measures thermal conductivity and precisely measures force applied. Reports derived thermal interface material resistances.

Note: ASTM D 5470-17 methodology may be purchased for a nominal fee from ASTM International. Information: www.astm.org



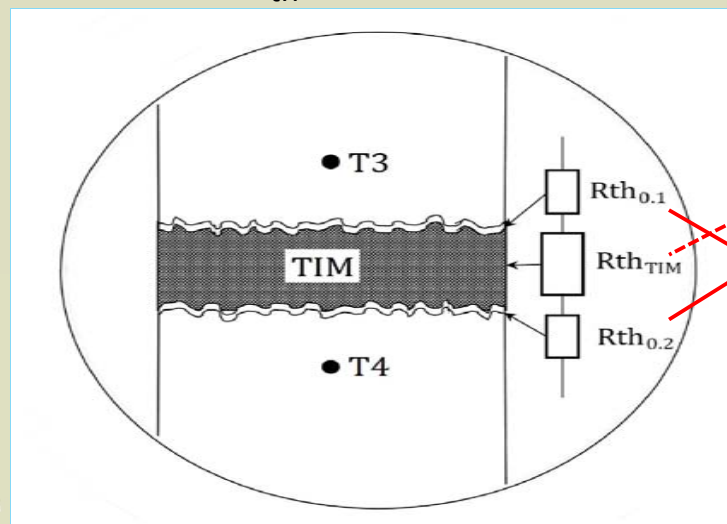


Thermal/Mechanical Test System Design

Thermal interface material testing with ASTM D 5470-17:

- Provides measurement of a thermal resistance value that is the sum of three constituent values:

The TIM thermal resistance *total* (R_{th}) is the important value, in practice.



TIM Bulk
Resistance

+

(2) Interfacial Contact Resistances
(Calculated)

=

TIM Thermal
Resistance (Total)

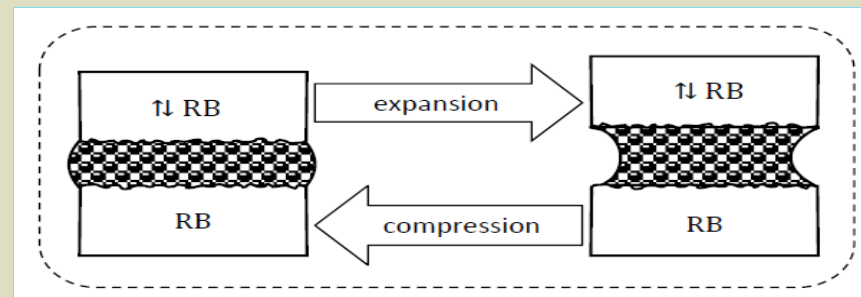
Cycling Reliability Testing: Berliner Nanotest Previous Work

- Mechanical cycling and other types of reliability testing over time can demonstrate useful results for evaluating TIMs.
- Previous reliability testing has been undertaken by Berliner Nanotest of “gap-filler” TIMs, examining cyclic compression and relaxation
- Certain of such TIMs may also be useful for test/burn-in – with different reliability testing requirements.
 - An example is the use of so-called “gap-filler” TIMs for testing with PCBs and other substrates.
 - The same test equipment described can be adapted for reliability testing of metallic TIMs with contact/dwell/release cycling.

Cycling Reliability Testing: Gap-Filler TIM

Examples: Examine long-term thermal and mechanical performance of TIMs.

- Mechanical compression/relaxation cycling of gap-fillers:

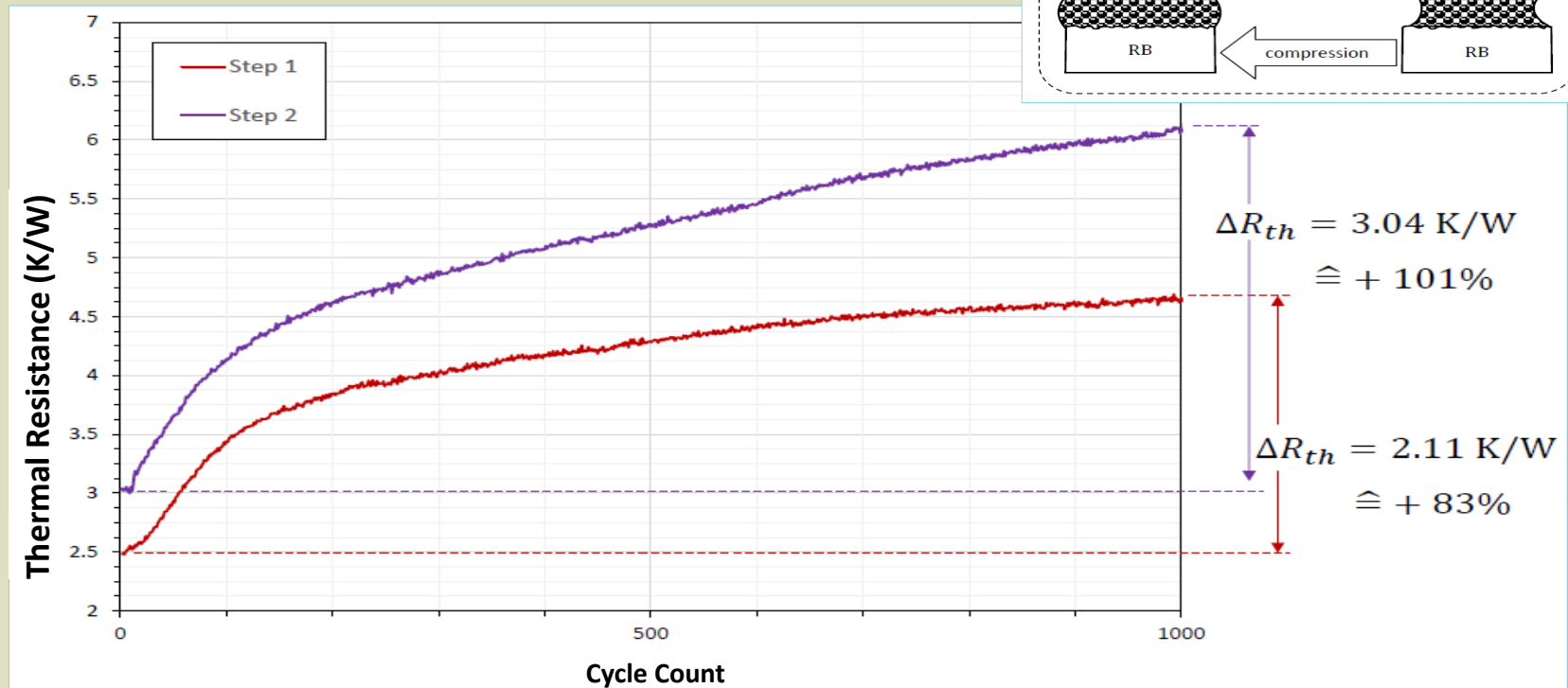


Data analysis:

- Evaluating for *time zero thermal resistance* values is *not adequate*;
- *Increasing thermal resistance over time* and cycling indicates a potential failure mechanism and increasing junction temperature.

Source: Berliner Nanotest und Design GmbH, 2018.

Cycling Reliability Testing: Gap-Filler TIM



Source: Berliner Nanotest und Design GmbH.

Phase I System Test Design: Parallel Test Heads

Reliability test data:

- The first phase of this test program is intended to establish a baseline of mechanical data with three types of TIMs;
- *Parallel* test heads;
- TIM (material under test) temperature: 95°C;
- Phase I testing includes three commercial TIM products designed to meet semiconductor test and burn-in market requirements;
- Success of Phase I program will determine if other TIM products will subsequently be tested.



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Phase I System Test Design: Parallel Test Heads

Test heads were developed for this mechanical cycling test program per the following specifications:

Table 5. Thermal /Mechanical Cycling Test Head Design	
Property	Value
Material	Aluminum Alloy (AlMgSi1)
Contact Area	17.5mm x 17.5mm (306mm ²)
Contact Surface Roughness	Rz ≤ 1μm
Sample Temperature	95°C
Upper Reference Body (Heater Bar)	125°C
Lower Reference Body (Liquid Cold Plate)	75°C
Temperature Measurement	In situ
Thickness Measurement Under Force Applied	In situ

Note: Uniform single clamping force and temperature applied for all materials. Data: Berliner Nanotest und Design GmbH, 2018.

Phase I System Test Design: Test Sample Materials

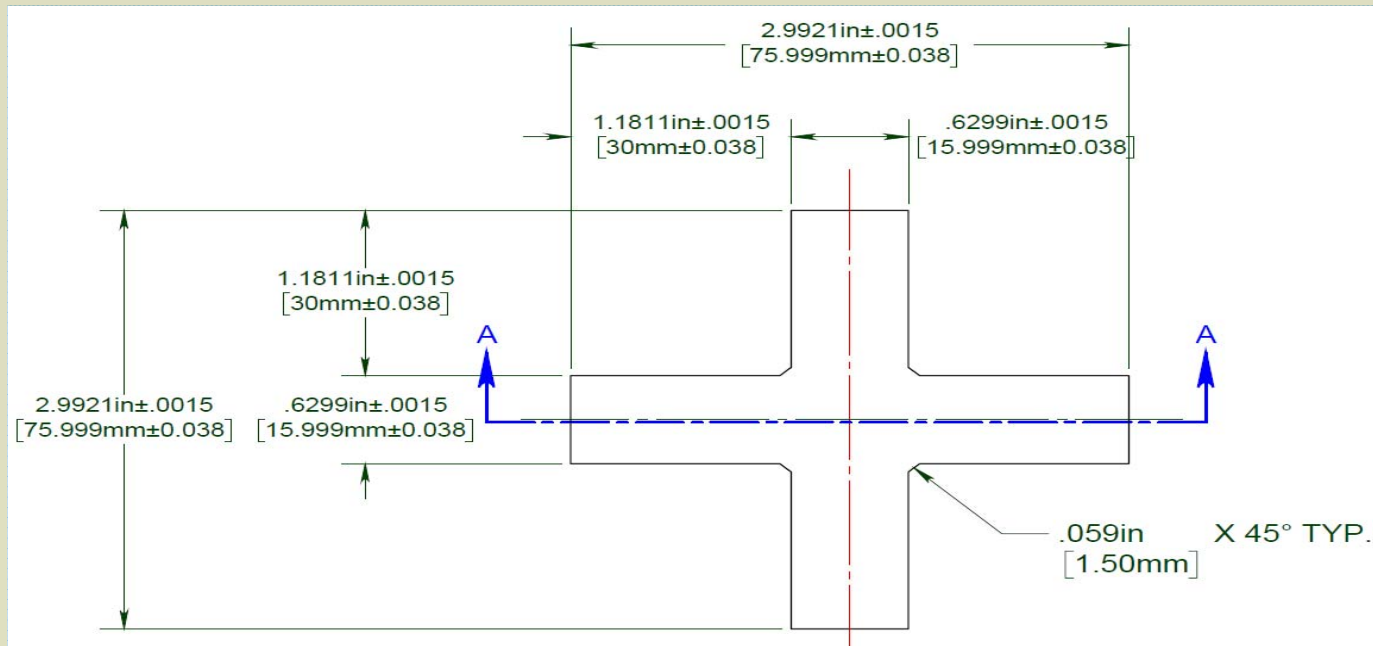
TIM commercial products developed for semiconductor test requirements, included in Phase I test program:

Table 6. Thermal Interface Materials Tested	
Graph Key	Description
CLAD	Indium (99.99%) flat foil, clad one side (0.0005") aluminum
CLAD HSK	Indium (99.99% foil, clad one side (0.0005") aluminum, HSK pattern applied*
HSMF-OS	Aluminum foil (0.002"), coated one side with dry thermal compound**

Note: * Indium Corporation Heat-Spring® HSK. ** Indium Corporation HSMF-OS.

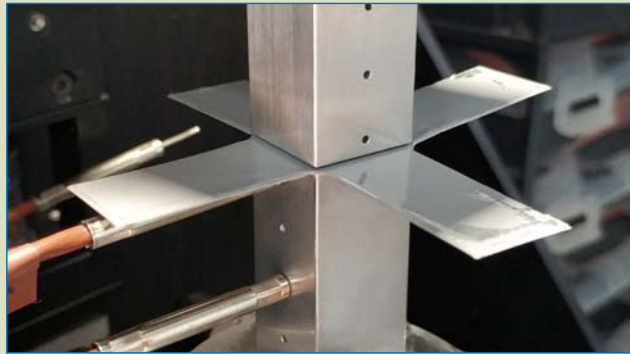
Phase I System Test Design: Test Sample Format

“Red Cross” test material designed for head attachment:



Phase I System Test Design: Test Sample Format

Test material attachment to test head:



Preparing to attach Al-clad TIM to upper test head for Phase I.



Inserting RTDs prior to Phase I start.

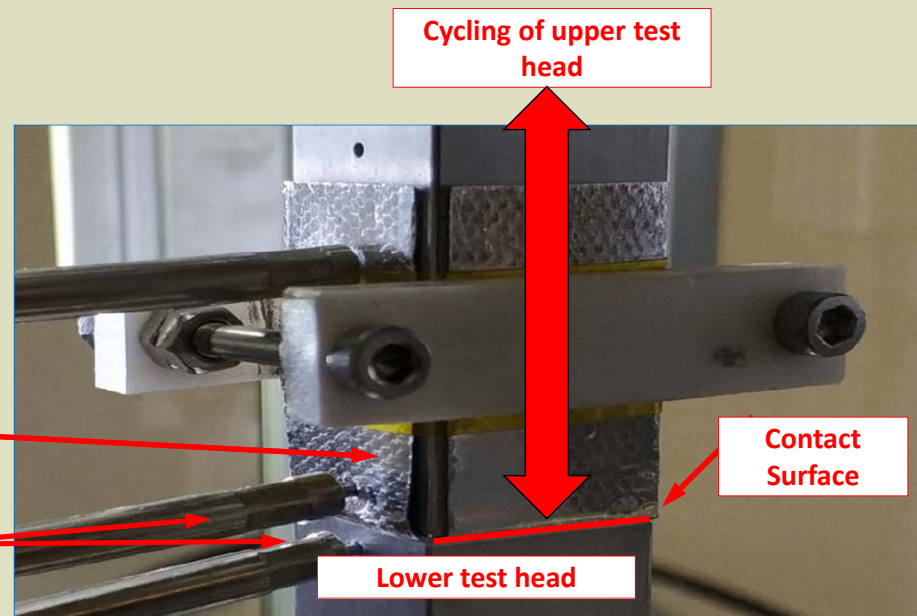
Phase I System Test Design: Parallel Test Heads

Test heads were adapted for this mechanical cycling test program to fit an existing test stand.

- Test assembly shown with TIM under test applied
- Heat-Spring® HSK aluminum-clad patterned indium alloy TIM applied to upper test head

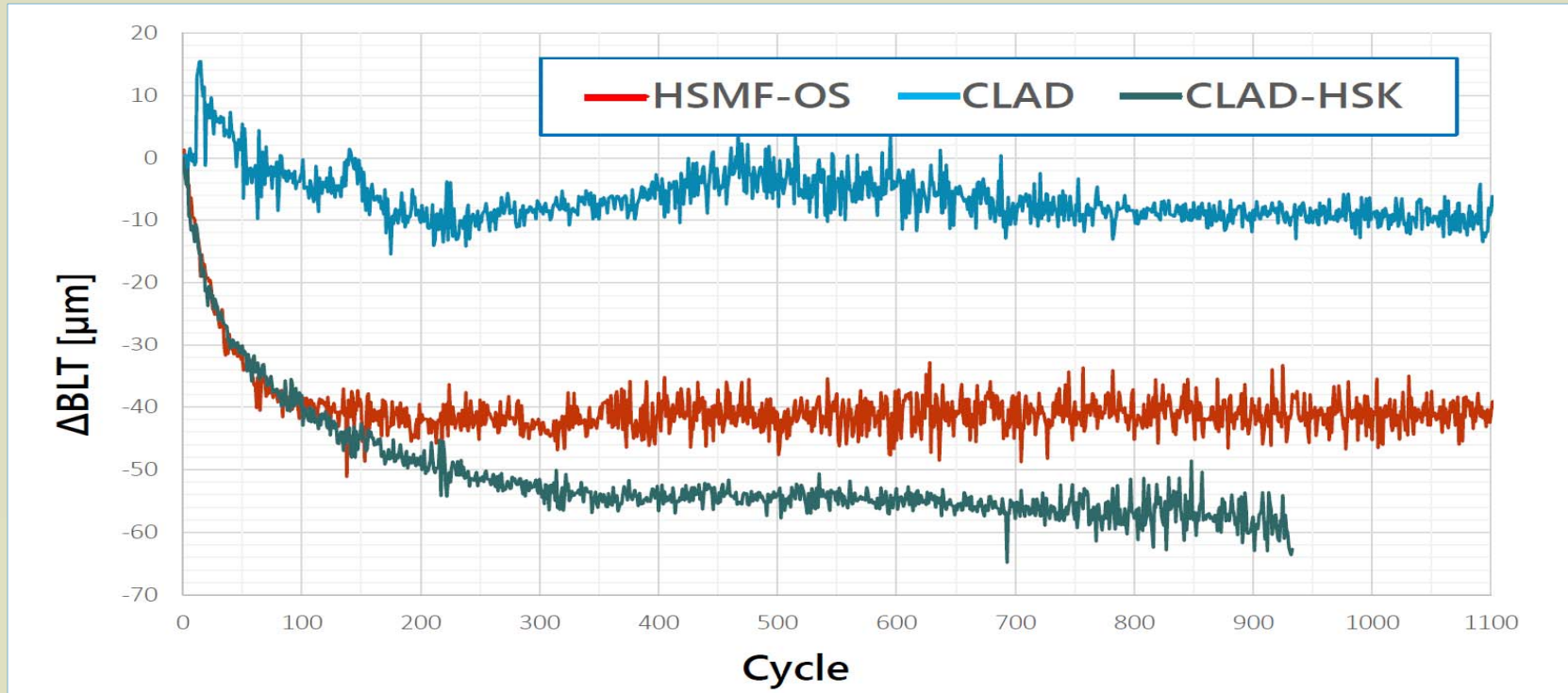
Upper test head with Clad HSK patterned indium foil TIM applied

RTDs inserted into test heads (3 places shown)



Note: Uniform single clamping force and temperature applied for all materials.

Test Data, Phase I: Thermal Resistance vs. Thickness Change



Source: Berliner Nanotest und Design GmbH.

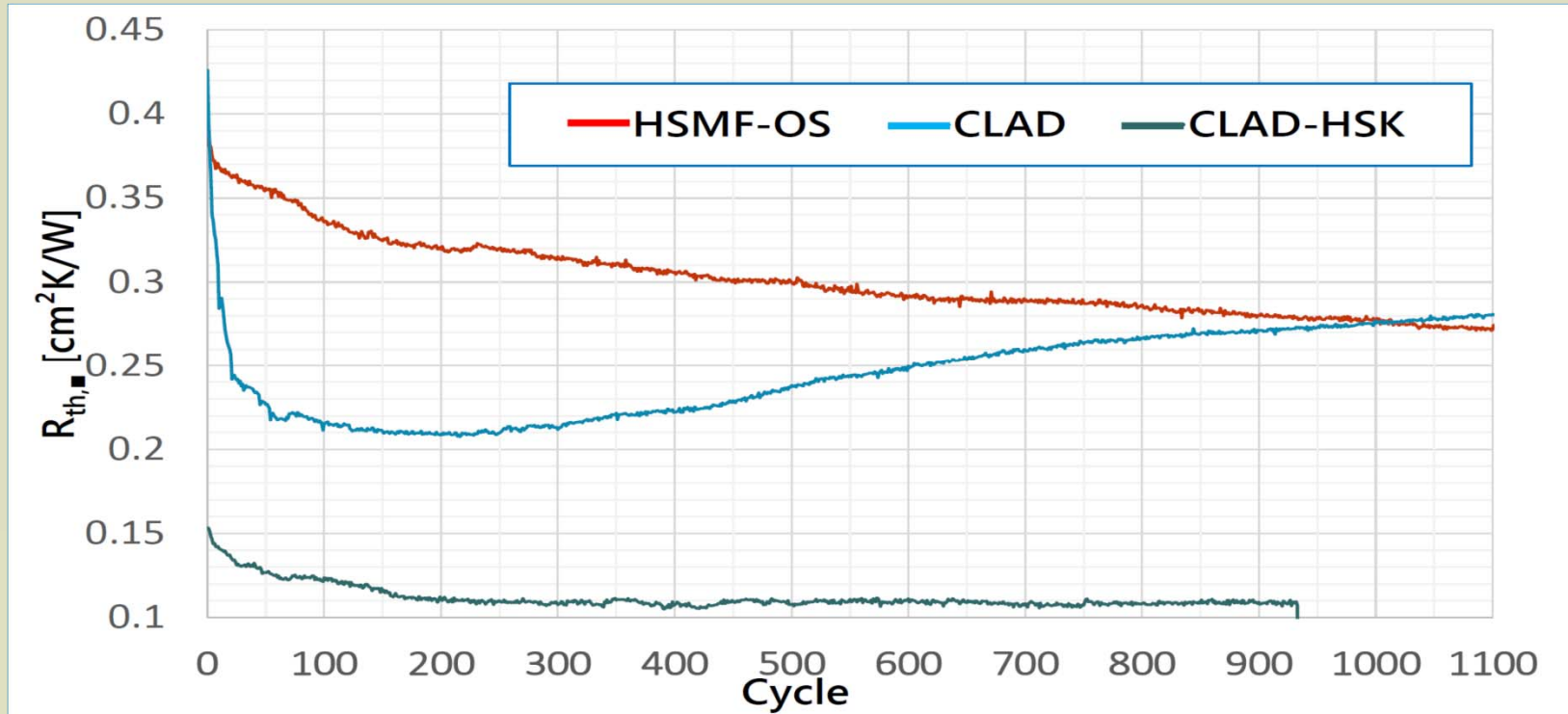
Note: Power supply failure at 940 cycles, CLAD-HSK material; test was subsequently completed successfully to >1,000 cycles.

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Test Data, Phase I: Thermal Resistance vs. Contact Cycling



Source: Berliner Nanotest und Design GmbH.

Note: Power supply failure at 940 cycles, CLAD-HSK material; test was subsequently completed successfully to >1000 cycles.

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Test Data, Phase I: Analysis

Phase I testing is intended to establish a baseline set of data to demonstrate:

- Mechanical cycling results with parallel test head surfaces, the most common application characteristic for semiconductor test;
- Thermal resistance during cycling: stable test values across full regime (*Note that this is a control mechanism only*);
- Thickness measurement during cycling: stable test values, full regime;
- Stable thermal resistance and thickness values fitting a typical test curve are important indicators of:
 - Properly performing, stable test platform and procedure;
 - Thermal and mechanical performance per expectations for values and shape of curve.



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Test Data, Phase I: Analysis

Phase I testing of all three TIM types successfully passed 1,300 cycles:

- HSMF-OS: 0.102mm (0.004")-thick aluminum foil, coated one side only with non-silicone thermal compound. Applied with Al surface facing DUT.
- 99.99% flat indium foil [0.30mm (0.012") thickness, including clad (one side only) with 0.1 μ m (0.0005") aluminum]. Applied to test head with aluminum surface facing DUT.
- Indium Corporation Heat-Spring[®] HSK patterned 99.99% indium foil, clad one side only with 0.1 μ m (0.0005") aluminum . Total thickness: 0.559mm (0.0220"). Applied to test head with bare aluminum surface facing DUT.

Test Data, Phase I: Observations

Phase I testing has demonstrated:

- Stable thermal resistance values achieved during mechanical cycling demonstrated *required durability* for all three baseline materials tested;
- Visual inspection indicated *no visible marking and zero residue* on lower body test head surface (*equivalent to the case or die surface of DUT*);
- Stable thermal and thickness values indicate that each material type has successfully passed test for long-term cycling without tearing or marking.



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Phase II System Test Design: Strike Angle

Phase II introduces an angled test head to create what is termed the “strike angle” in semiconductor test and burn-in:

- Test head w/TIM applied strikes at 7.5° angle, creating a knife edge contact for the TIM to the second test head;
- Stable thermal resistance values achieved during mechanical cycling demonstrated required durability for all three baseline materials tested;
- Visual inspection indicated *no visible marking and zero residue* on lower body test head surface (equivalent to the case or die surface of DUT);
- Stable thermal and thickness values indicate success of each material type for long-term cycling *without tearing or marking*.



Mechanical Cycling Reliability Test Program for Semiconductor Test

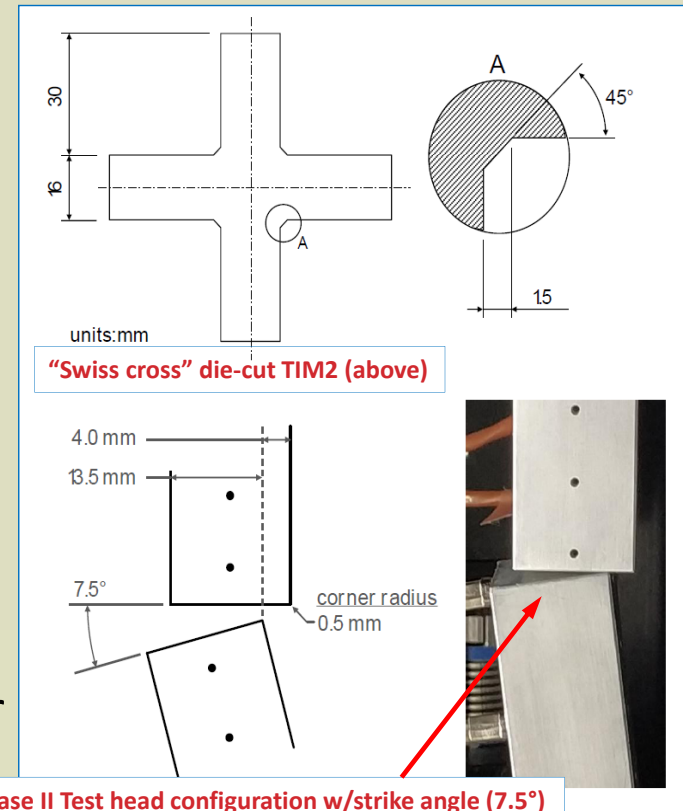
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Phase II System Test Design: Strike Angle

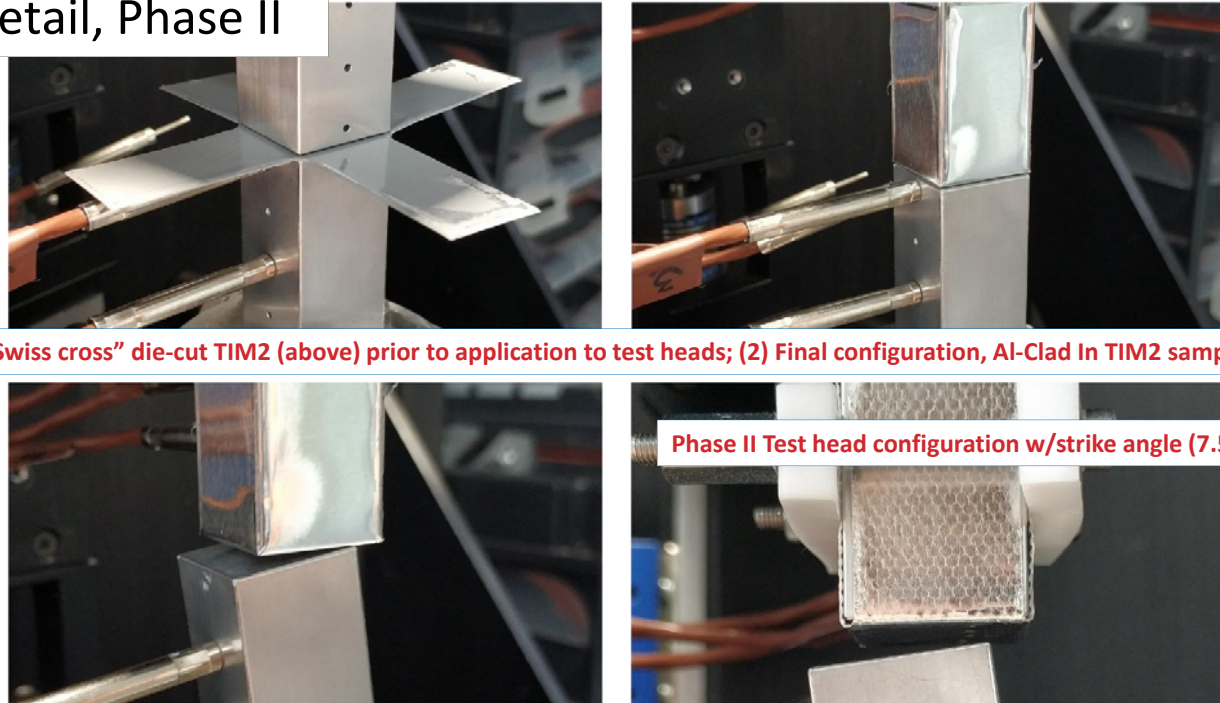
Test heads were adapted for this mechanical cycling test program to fit existing test stand.

- Test assembly shown with TIM under test applied as “Swiss Cross”;
- Test head (lower) strikes test head (upper) at 7.5° angle, to mimic actual conditions;
- TIM applied to upper test head;
- Nanotest TIMA5 test stand is servo-driven, enabling use of this test stand to test with automated mechanical cycling for repeated, precise contact control.



Phase II System Test Design: Strike Angle

Test head detail, Phase II

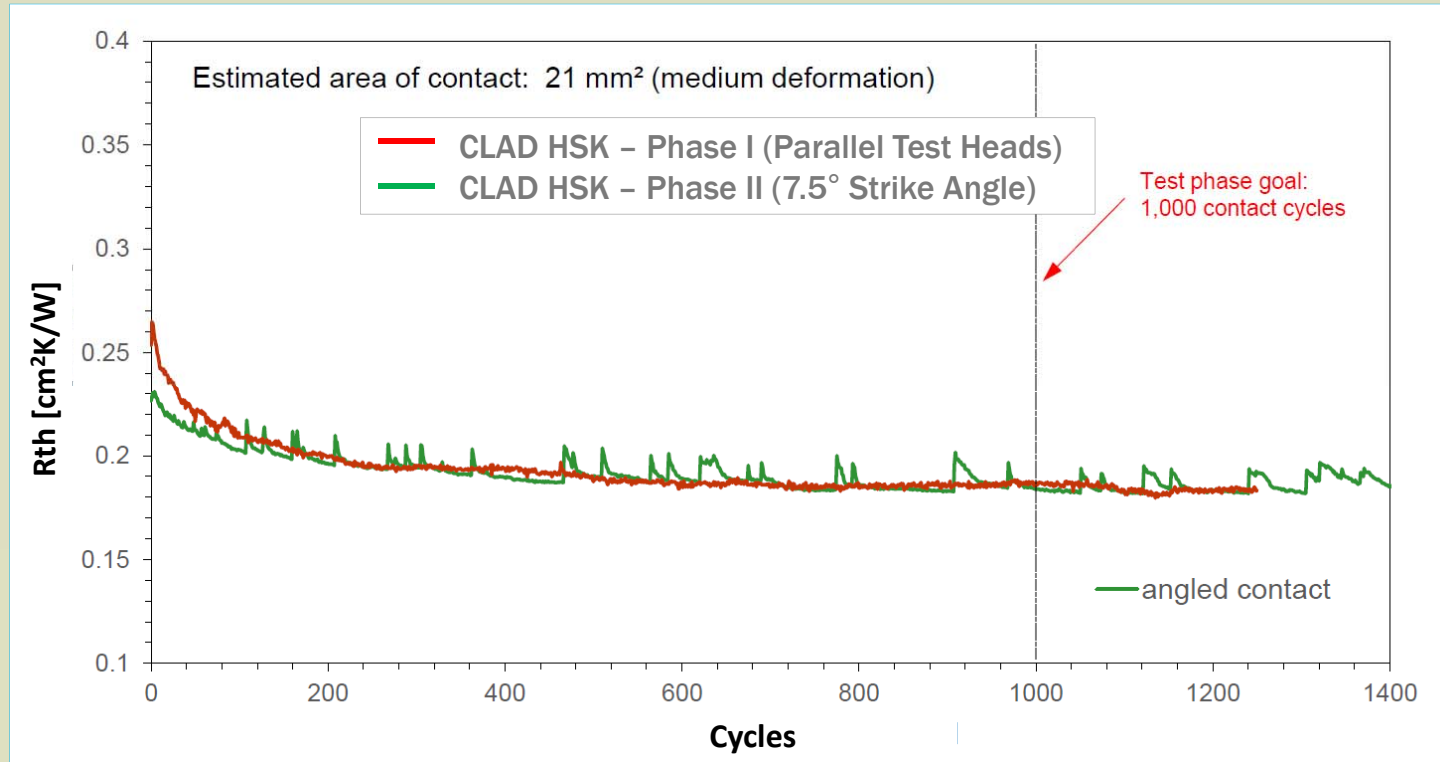


(1) "Swiss cross" die-cut TIM2 (above) prior to application to test heads; (2) Final configuration, Al-Clad In TIM2 sample.

Phase II Test head configuration w/strike angle (7.5°)

(3) Strike angle, lower test head – TIM2 applied to upper head (above); (4) Final configuration, In "Heat-Spring" TIM2.

Phase II System Test Design: Strike Angle



Source: Berliner Nanotest und Design GmbH. Initial data report, October 10, 2018.

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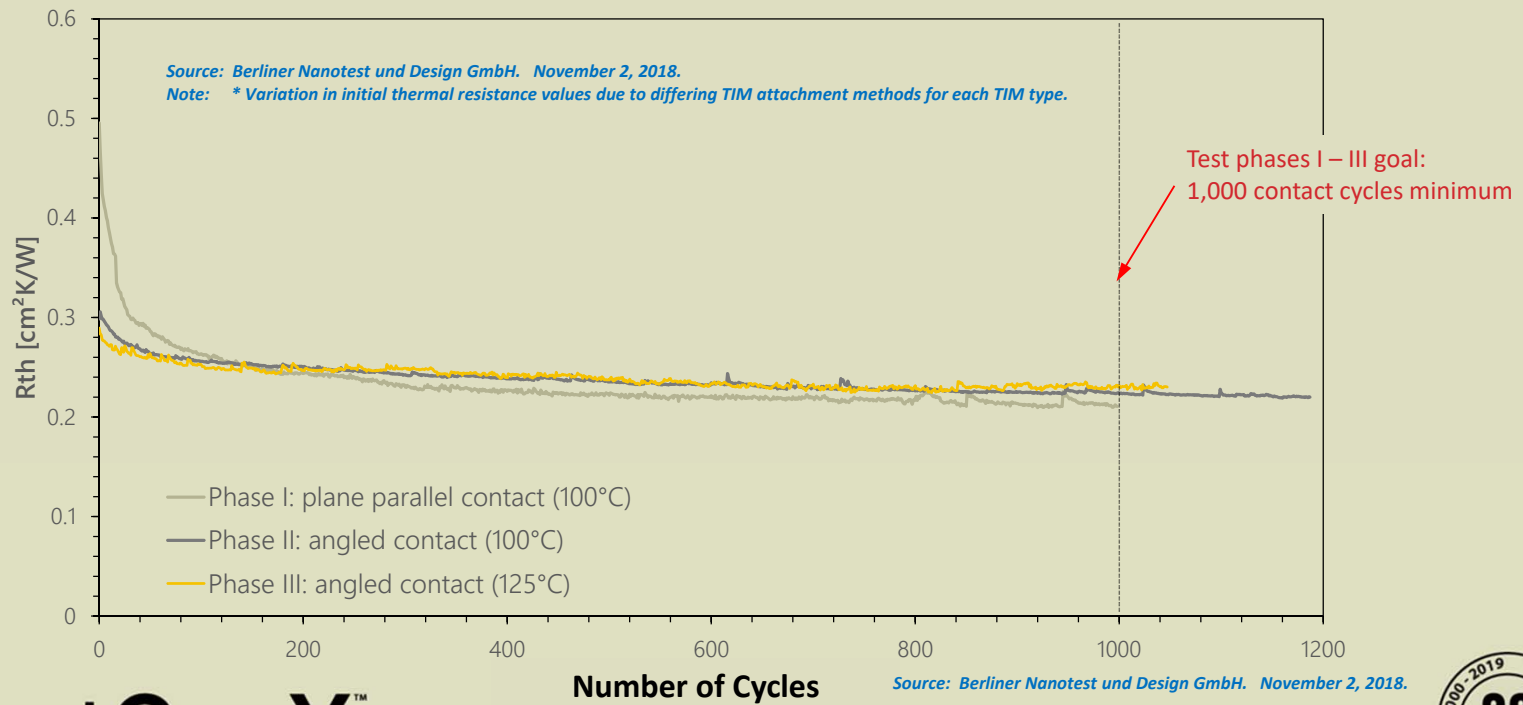
Phase III System Test Design: Strike Angle + High Temperature

This phase consists of the introduced strike angle and identical test routine at higher temperature:

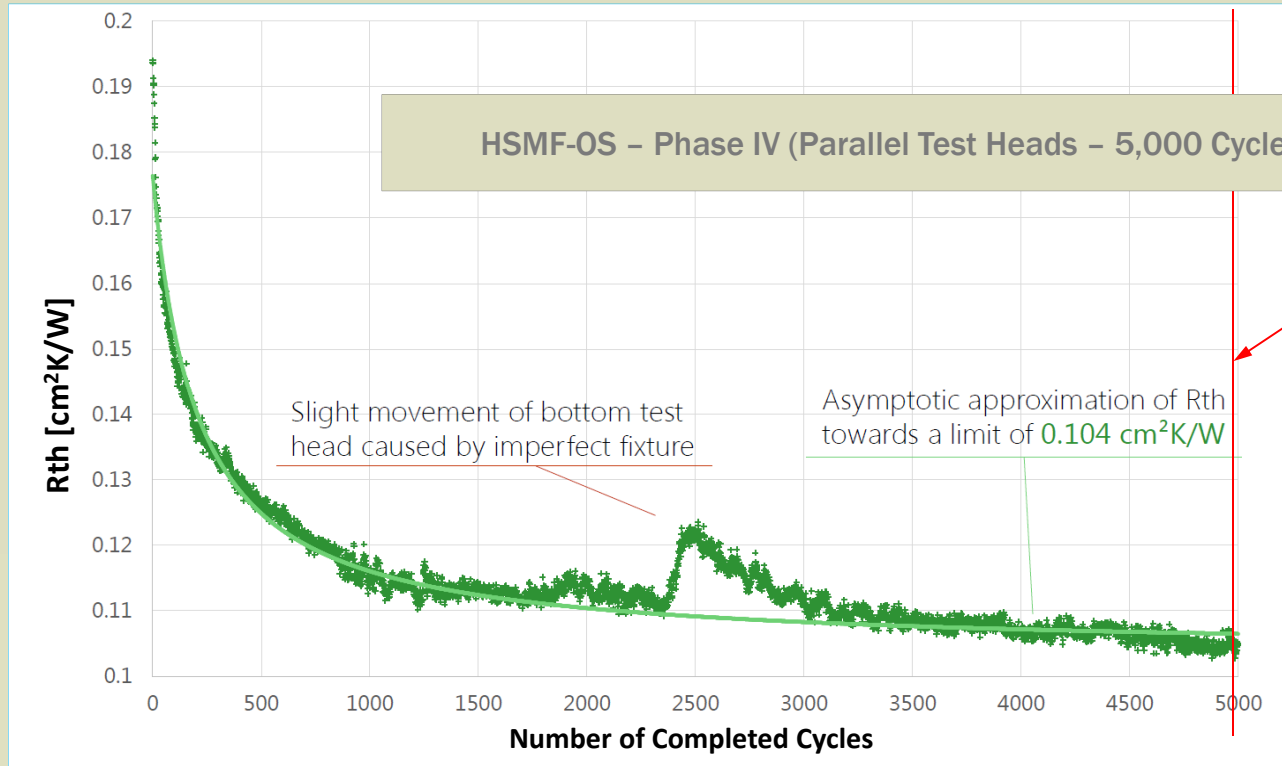
- 125C test temperature applied at the test head;
- Characteristic of semiconductor burn-in temperatures;
- Characteristic of test system designs incorporating a gimbaled head, for contact with multiple package sizes and types. Examples:
 - Lidded processor or ASIC;
 - Bare die packages with different die sizes, lot to lot.
- *Please keep in mind that this test system is intended to be a mechanical durability test; as such, thermal resistance values generated are solely a control mechanism.*

Phase III System Test Design: Strike Angle + High Temperature

Initial test data report, Phase III*:



Phase IV System Test Design: Parallel Heads, 5,000 Cycles



Source: Berliner Nanotest und Design GmbH; November 2, 2018.



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Summary

Thermal interface materials (TIM) are integral for adequate heat transfer from a semiconductor source to an external environment.

- Specialized TIM materials can be characterized as “well-performing” when measured against challenging requirements for critical applications.

A range of metallic TIMs developed for specialized semiconductor test applications requiring performance and reliability in challenging conditions.

- A mechanical cycling reliability test program has been designed to reproduce semiconductor test conditions to determine robustness of specialized TIMs:
 - Phases I - IV of this test program have been completed.
 - All materials tested passed all cycling test goals successfully. Data analysis is reported.



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